

**NAGAHAMA et al**  
**Serial No. 09/500,288**

**REMARKS**

Claim 9 is amended to further define the invention. The relative coefficient of expansion is disclosed on page 13, lines 15-18 and claim 2 and the result of providing compression strain on the device forming layer at page 13, lines 19-20.

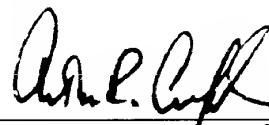
Consideration of this amendment and the Information Disclosure Statement filed March 28, 2002 is requested.

Attached hereto is a marked-up version of the changes made to the claim by the current amendment. The attached page is captioned "**Version With Markings To Show Changes Made.**"

Respectfully submitted,

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS

9. (Amended) A nitride semiconductor laser comprising  
a GaN substrate having a single-crystal GaN layer at least on its surface and  
device-forming layers made of nitride semiconductor that are formed on said  
GaN substrate and are devoid of small cracks,  
wherein said single-crystal GaN layer is formed through a lateral-growth process;  
and  
said device-forming layer contacting said GaN substrate is made of  
Al<sub>a</sub>Ga<sub>1-a</sub>N(0<a≤1) and has a coefficient of thermal expansion less than that of the GaN  
substrate thereby providing compression strain on the device-forming layer.